Generation and Detection of Surface Plasmon Polaritons by Transition Metal Dichalcogenides for Chip-level Electronic-Photonic Integrated Circuits

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Subject Areas: Optoelectronics, plasmonics, nanophysics
Abstract

The monolithic integration of electronics and photonics has attracted enormous attention due to its potential applications. However, the realization of such hybrid circuits has remained a challenge because it requires optical communication at nanometer scales. A major challenge to this integration is the identification of a suitable material. After discussing the material aspect of the challenge, we identified atomically thin transition metal dichalcogenides (TMDs) as a perfect material platform to implement the circuit. The selection of TMDs is based on their very distinct property: monolayer TMDs are able to emit and absorb light at the same wavelength determined by direct exciton transitions. To prove the concept, we fabricated simple devices consisting of silver nanowires as plasmonic waveguides and monolayer TMDs as active optoelectronic media. Using photoexcitation, direct optical imaging and spectral analysis, we demonstrated generation and detection of surface plasmon polaritons by monolayer TMDs. Regarded as novel materials for electronics and photonics, transition metal dichalcogenides are expected to find new applications in next generation integrated circuits.
The monolithic integration of electronic and photonic circuits would not only increase the speed of computation with reduced power consumption, but also provides new applications such as quantum information processing and chemical or biological sensing. The idea of developing an electronic photonic integrated circuit (EPIC) dates back decades after great successes of silicon microelectronics and fiber-based optical communication. Silicon is a natural choice of material for EPIC because of its mature technology, but silicon is an indirect bandgap semiconductor which makes it difficult to fabricate optoelectronic devices. In the so-called silicon photonics, much effort has been made to transform silicon to an active optical material for light generation and detection, especially in the sub-bandgap wavelength range so that silicon itself can be used as optical waveguide [1-4]. There are also hybrid approaches to implementing board-level EPIC, for instance, by creating a Raman laser using optical pumping, or by integration with III-V devices [5, 6]. Much attention has recently been shifted to chip-level EPIC – electronic plasmonic integrated circuit, because sub-wavelength confinement of light enables miniaturization of photonic circuits on a similar nanometer scale to electronics [7-10]. Several groups have demonstrated integrating semiconductor electro-optical components with surface plasmons on metallic structures. For example, Falk et al. demonstrated local electrical detection of surface plasmon polariton (SPP) using Ge nanowires [11]; Neutens et al. utilized an integrated GaAs photodetector to detect gap SPP [12]; Direct SPP generation by electricity has also been realized through nanometer scale light-emitting diodes using III-V semiconductors [13-15]. Despite significant progresses achieved in both silicon photonics and plasmonics, a primitive integrated circuit with basic on-chip optical communication between transistors has not been demonstrated.

We believe that the challenge to EPIC is essentially a material issue. While silicon is not an excellent candidate due to its nature of indirect bandgap, a direct bandgap semiconductor is not necessarily sufficient for EPIC either even though it is ideal for both electronics and
Taking the above-mentioned device as an example, although SPP can be directly generated by a nanoscale integrated GaAs diode [13, 14], it can hardly be detected using the same GaAs because optical absorption at the band edge of GaAs is negligible. This asymmetry between strong light emission and weak optical absorption at the band edge is a fundamental property of conventional semiconductors and has made them very difficult to implement EPIC. Here we identify two-dimensional (2D) transition metal dichalcogenides (TMDs) as the material of choice for EPICs because monolayer TMDs are able to emit and absorb light at the same wavelength determined by direct exciton transition [16, 17], thus the conversion between electrical and optical information, i.e., on-chip optical communication could be realized on the same material platform.

Two-dimensional TMDs have emerged as promising nanomaterials for both electronic and photonic device applications [17-23]. However, it is the unique exciton resonances in optical emission and absorption that distinguish monolayer TMDs from conventional semiconductors [16, 17, 24, 25]. Such an atom-like emission-absorption relationship is enabled by large exciton binding energy and direct exciton transition in monolayer TMDs [16, 17, 24]. The generation of SPP at exciton wavelength in monolayer MoS$_2$ has recently been reported, but the studies failed to distinguish MoS$_2$ from thin films of conventional optical materials [26, 27]. By monitoring spectral and intensity evolutions of SPP propagating along the plasmonic waveguide on TMDs, we have not only separated absorption by monolayer TMDs from propagation loss due to plasmonic waveguide, but also revealed that absorption of SPP exhibits the same exciton resonance as in photoluminescence. This demonstration of generation and detection of SPP at the same exciton wavelength – nanoscale optical communication, paves the way for chip-level fully integrated electronic-photonic circuits.
Fig. 1a shows a representative device configuration and experimental setup. Large-size monolayer WS$_2$ and MoS$_2$ are synthesized by chemical vapor deposition [28, 29]. Ag nanowires with a diameter of ~120 nm (Agnw-120 from ACSMATERIAL) are used as plasmonic waveguide and are directly placed on single crystals of monolayer TMD on a SiO$_2$/Si substrate. A 532-nm laser is used to photoexcite monolayer TMD through a microscopy objective. The generation and propagation of SPP can be clearly seen from the luminescence images in Fig. 1b-d. When the travel distance of SPP increases, its intensity becomes weaker due to propagation loss from Ag nanowire. This intensity attenuation of SPP is also confirmed by the corresponding spectra shown in Fig. 1f. However, unlike previous studies of SPP on MoS$_2$ [26, 27], the spectrum of WS$_2$ SPP experiences a noticeable redshift: the longer the propagation distance, the larger the spectral shift. Fig. 1e further confirms that the propagation of SPP is always associated with a spectral redshift. What’s surprising here is that the 1A SPP experiences a larger spectral redshift than 1B SPP although 1A SPP travels a shorter distance than 1B SPP.

To understand the origin of the spectral shift, we normalize the spectrum of SPP with respect to the photoluminescence spectrum of WS$_2$, the results are shown in Fig. 1g. As can be seen, both spectra exhibit a gradual decrease in spectral loss at longer wavelengths and a resonant absorption near 625 nm, but the resonant absorption in spectrum 1A is more pronounced than that of 1B. We attribute the broad absorption to the SPP propagation loss from the Ag nanowire [30], and the resonant absorption to WS$_2$. The weaker WS$_2$ absorption for 1B SPP is due to its shorter interaction length with WS$_2$ because less than half of the distance is above the WS$_2$. To obtain a better resonant absorption spectrum with less background from the nanowire propagation loss, we normalize the spectrum of 3B using the spectrum of 1B as a reference, the result in Fig. 1h shows a clear resonance with less background. The SPP absorption spectrum exhibits an excellent overlap with photoluminescence spectrum,
indicating that both SPP absorption and photoluminescence originate from the same exciton transition in WS$_2$.

Similar spectral shift and resonant absorption of SPP can also be observed in MoS$_2$, as shown in Fig. 2. Despite the close proximity of B exciton, the spectrum of MoS$_2$ SPP is still dominated by A exciton. Fig. 2d clearly shows the overall loss from the waveguide and MoS$_2$: when the propagation distance of SPP increases, both the nanowire propagation loss and resonant exciton absorption becomes pronounced.

These two separate contributions to propagation loss of SPP are also confirmed and quantified by carefully studying the dependence of the loss on the SPP travel distance. Fig. 3a shows the experimental setup. Taking WS$_2$ as an example, when an SPP is created by photoexcitation, it will go through two regions before reaching the clear end of the waveguide: the first region is the nanowire on WS$_2$, and the second one is the nanowire alone. We designate $\alpha_1$ and $\alpha_2$ as the absorption coefficients due to the nanowire and WS$_2$, respectively. The total absorption coefficient when the nanowire on WS$_2$ can be approximated as

$$\alpha = \alpha_1 + \alpha_2.$$  

Thus, the end emission at the point $x$ can be expressed as

$$I(x) = I_0 e^{-\alpha_1(x-d)} e^{-\alpha_2x} = I_0 e^{-\alpha_1(x-d)} e^{-\alpha_2x}$$  

(1)

Here $I_0$ is the intensity of the exciton SPP at the point of photoexcitation. If we define propagation length $L_1$ and $L_2$ as $L_1 = 1/\alpha_1$, $L_2 = 1/\alpha_2$, then the equation can be written as

$$I(x) = I_0 e^{-(\alpha_1+\alpha_2)(x-d)} e^{-\alpha_2x} = I_0 e^{-(x-d)/L_1} e^{-x/L_2}$$  

(2)

The propagation lengths $L_1$ and $L_2$ can be obtained by curve fitting equation 2. Figure 3b–c shows the excitation images of two devices. Figure 3d shows a series of snapshots of SPP photoexcitation and SPP end emission in a third device. The integrated SPP intensity is plotted in Figure 3e as a function of SPP travel distance. Curve fitting by equation 2 gives us $L_1 = 2.2 \mu m$ and $L_2 = 8.6 \mu m$. The propagation length $L$ of SPP with the nanowire on WS$_2$ is
~1.8 \textmu m based on the total absorption of $\alpha_1 + \alpha_2$. Similar propagation lengths are also obtained from the other two devices in Figure 3b–c. The propagation length $L_2$ is similar to previous reported values using silver nanowires with a similar diameter.[30-34]

Exciton resonance is a general and unique characteristic of all monolayer TMDs, it is manifested by sharp spectra of luminescence and absorption at the same peak wavelength [16, 17, 24, 25], similar to those observed in atomic spectra. In fact, large exciton binding energy in monolayer TMDs makes it behave like an artificial atom. To further characterize WS$_2$ and MoS$_2$ monolayers and to better understand the origin of SPP absorption, we measured their differential reflectance spectra, which are equivalent to absorption spectra. Near perfect spectral overlaps between differential reflectance and photoluminescence spectra can be seen in Fig. 4a-b, indicating the high quality of monolayers and confirming that the same exciton transition is responsible for the resonant absorption of SPPs.

The understanding of SPP absorption allows us to numerically calculate the propagation length based on the measured optical constants of TMDs [35]. Note that the strong absorption of SPP by TMD monolayer is also a result of plasmon-enhanced strong light-matter interaction. Figure 4c shows the local field distribution around the nanowire/WS$_2$ at 633 nm, which is close to the wavelength of WS$_2$ SPP. This is the fundamental mode of SPP, and it has been previously studied without a WS$_2$ monolayer [33, 34, 36]. Although only one monolayer thick, the effect of monolayer WS$_2$ is noticeable: the field becomes more concentrated in the region where the nanowire and WS$_2$ overlap, leading to a short propagation length. Figure 4d shows the dependence of SPP propagation length on nanowire diameter with and without WS$_2$. It can be seen that the effect of WS$_2$ is strong regardless of the nanowire diameter. For the 120-nm nanowire, we obtain a propagation length of 2.4 \textmu m, in good agreement with the experimental value.
For a complete EPIC, SPPs should be generated and detected locally by electrical means and no external light source should be used. This integration can be envisioned based on recent demonstrations of TMD-based optoelectronic devices. For example, the exciton SPP generation can be readily implemented by using light-emitting diodes (LEDs) [22, 23]. In fact, our configuration of plasmonic nanowire on a flat TMD is totally compatible with the configuration of these LEDs. Similar structures can also be used to make SPP photodetectors. TMDs also offer other flexibility. For example, the SPP wavelength can be selected by choosing different TMDs, or tuned by strain or doping [37]. Here chemically synthesized Ag nanowires are used only to demonstrate the concept, and lithographically defined plasmonic waveguides and couplers should be used for large-scale integration [15, 32].

In conclusion, we demonstrated the generation and subsequent detection of SPPs by monolayer TMDs at the same wavelengths determined by direct exciton transitions. Although the generation and detection were observed optically, the device can be readily modified to perform local generation and detection of SPPs by electrical means, i.e., nanoscale optical communication between transistors on the same chip. Because planar structure of 2D TMDs is compatible with the current lithographic fabrication process, we expect the demonstration of a complete EPIC in a not too distant future.

References:


Figure Captions

FIG. 1. Absorption spectrum of exciton surface plasmon polariton (SPP) by WS₂. (a) Excitation image of the device. (b) Luminescence image of (a). (c–d) Luminescence images when WS₂ is photoexcited at two other locations along the Ag nanowire. (e) Photoluminescence spectrum of WS₂ away from the nanowire (black), and SPP spectra from point 1A and 1B in Fig. 1b. Spectra are normalized to have the same peak intensity. (f) SPP spectra from 1B, 2B, and 3B in Figs. 1b-d. (g) Ratios of the spectra 1B and 1A to the exciton spectrum of WS₂. (h) Ratio of spectrum 3B to spectrum 1B (red), in comparison to the spectrum of WS₂. Scale bars: 3 µm.

FIG. 2. Absorption spectrum of exciton SPP by MoS₂. (a-b) Luminescence and excitation images of the device. (c) Spectra of SPPs from the photoexcitation and nanowire end. Spectra are normalized to have the same peak intensity. (d) Ratios of the SPP spectra from the nanowire end to the spectra from the photoexcitation. Inset shows the locations of photoexcitation along the waveguide on MoS₂. Location #2 is responsible for the spectra in Fig. 2a-c.

FIG. 3. Propagation length of exciton SPP. (a) Schematic of the experimental design. (b–c) Optical images of two devices. (d) Photoexcitation (top) and SPP emission images (zoomed-in images at the bottom) of a third device. (e) Intensity of the SPP end emission based on (d) as a function of distance between the photoexcitation and emission. The dashed line is the fit. Scale bars: 5 µm.

FIG. 4. Resonant absorption by exciton and calculation of propagation length of exciton SPP. (a-b) Differential reflectance spectra and photoluminescence spectra of WS₂ (a) and MoS₂ (b). (c) A cross-sectional view of a field intensity profile of propagating SPP at 633 nm. The diameter of nanowire is 120 nm. (b) Calculated SPP propagation lengths along the Ag nanowire as a function of the nanowire diameter with and without WS₂.
Figures

![Fig. 1](image-url)
FIG. 2
FIG. 3

\( d = 3.5 \, \mu m \)

\[ I(x) = I_0 \times e^{-\frac{(x-d)}{L_1}} \times e^{-\frac{x}{L_2}} \]

\( L_1 = 2.2 \, \mu m \)

\( L_2 = 8.6 \, \mu m \)
FIG. 4